

IN THE TITLE

Please delete the title in its entirety and insert --- METHOD OF DETERMINING POST-ETCH OFFSET IN EXPOSED-TO-EMBEDDED OVERLAY --- therein.

IN THE CLAIMS

Please cancel claims 1-12 without prejudice.

Please enter the pending claims as follows:

1. - 12. (Canceled)

13. (Original) A method comprising:

forming a first set and a second set of features in a substrate;

covering said first and second set of features with material;

forming a third set of features in said material and removing said material to expose said first set of features, leaving said second set of features embedded below said material;

measuring post-etch overlay between said first set and said third set of features; and

measuring post-develop overlay between said second set and said third set of features.

14. (Original) The method of claim 13 further measuring an exposed-to-embedded offset between said first set and said second set of features.

15. (Original) The method of claim 14 wherein said exposed-to-embedded offset corrects subsequent measurements of post-develop overlay to predict post-etch overlay.

16. (Original) The method of claim 13 wherein said material is transparent.

17. (Original) The method of claim 13 wherein said material is opaque.

18. (Original) A method comprising:

determining centerline of a first set of features formed in a substrate and not covered with a material;

determining centerline of a second set of features formed in said substrate and covered with said material, said second set and said first set of features being formed together in said substrate;

determining centerline of a third set of features formed in said material;

determining overlay of said third set to said first set of features; and

determining overlay of said third set to said second set of features;

19. (Original) The method of claim 18 further determining overlay of said first set to said second set of features.

20. (Original) The method of claim 18 wherein said centerline is determined optically.